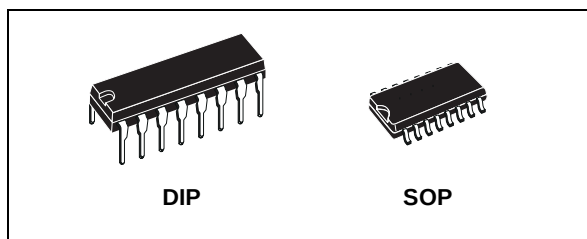




HCF4051B

SINGLE 8-CHANNEL ANALOG MULTIPLEXER/DEMULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.)
OVER 15V p.p SIGNAL-INPUT RANGE FOR
 $V_{DD} - V_{EE} = 15V$
- HIGH "OFF" RESISTANCE : CHANNEL
LEAKAGE $\pm 100pA$ (Typ.) at $V_{DD} - V_{EE} = 18V$
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY : < 0.5%
DISTORTION TYP. at $f_{IS} = 1KHz$, $V_{IS} = 5 V_{pp}$,
 $V_{DD} - V_{SS} \geq 10V$, $R_L = 10K\Omega$
- VERY LOW QUIESCENT POWER
DISSIPATION UNDER ALL DIGITAL
CONTROL INPUT AND SUPPLY
CONDITIONS : 0.2 μW (Typ.)
at $V_{DD} - V_{SS} = V_{DD} - V_{EE} = 10V$
- MATCHED SWITCH CHARACTERISTICS :
 $R_{ON} = 5\Omega$ (Typ.) FOR $V_{DD} - V_{EE} = 15V$
- WIDE RANGE OF DIGITAL AND ANALOG
SIGNAL LEVELS : DIGITAL 3 to 20,
ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIFIED UP TO
20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 $I_I = 100nA$ (MAX) AT $V_{DD} = 18V$ $T_A = 25^\circ C$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC
JESD13B " STANDARD SPECIFICATIONS
FOR DESCRIPTION OF B SERIES CMOS
DEVICES"



ORDER CODES

PACKAGE	TUBE	T & R
DIP	HCF4051BEY	
SOP	HCF4051BM1	HCF4051M013TR

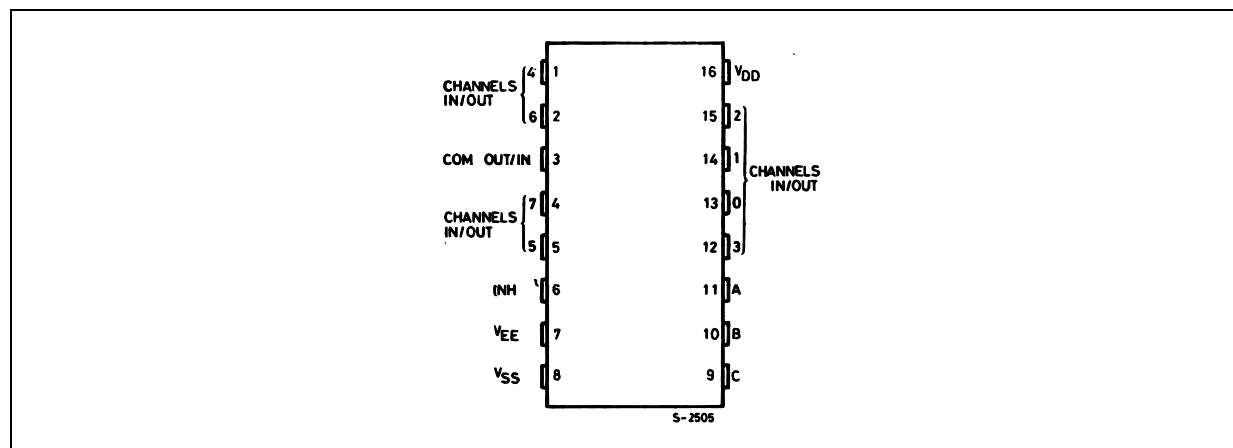
DESCRIPTION

The HCF4051B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages.

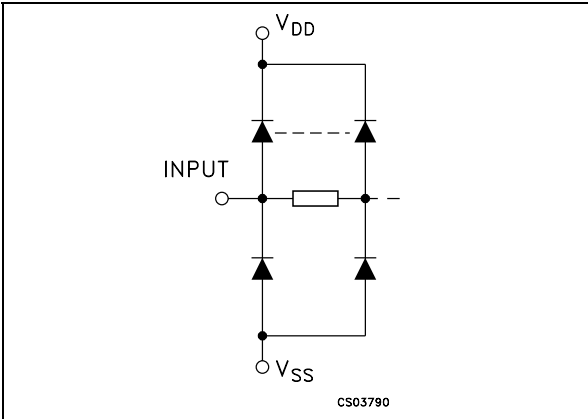
The HCF4051B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full $V_{DD} - V_{SS}$ and $V_{DD} - V_{EE}$ supply voltage range, independent of the logic state of the control signals.

When a logic "1" is present at the inhibit input terminal all channel are off. This device is a single 8-channel multiplexer having three binary control inputs, A, B, and C, and an inhibit input. The three binary signals select 1 of 8 channels to be turned on, and connect one of the 8 inputs to the output.

PIN CONNECTION



INPUT EQUIVALENT CIRCUIT



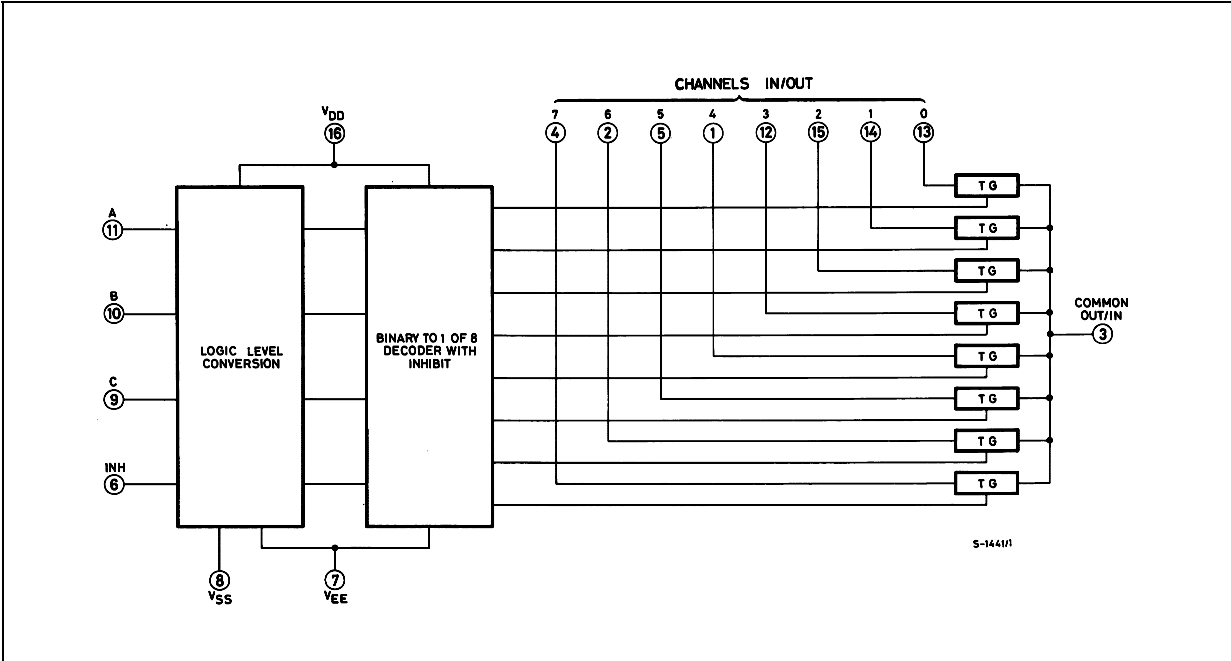
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
11, 10, 9	A, B, C	Binary Control Inputs
6	INH	Inhibit Inputs
13, 14, 15, 12, 1, 5, 2, 4	0 to 7 CHANNEL IN/OUT	Indipendent inputs/out-puts
3	COM OUT/IN	Common Output/Input
7	V_{EE}	Supply Voltage
8	V_{SS}	Negative Supply Voltage
16	V_{DD}	Positive Supply Voltage

TRUTH TABLE

INPUT STATES				"ON" CHANNEL (S)
INHIBIT	C	B	A	
0	0	0	0	0
0	0	0	1	1
0	0	1	0	2
0	0	1	1	3
0	1	0	0	4
0	1	0	1	5
0	1	1	0	6
0	1	1	1	7
1	X	X	X	NONE

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V_I	DC Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	°C
T_{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value								Unit
		V _{IS} (V)	V _{EE} (V)	V _{SS} (V)	V _{DD} (V)	T _A = 25°C			-40 to 85°C		-55 to 125°C			
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
I _L	Quiescent Device Current (all switches ON or all switches OFF)				5		0.04	5		150		150	μA	
					10		0.04	10		300		300		
					15		0.04	20		600		600		
					20		0.08	100		3000		3000		
SWITCH														
R _{ON}	Resistance	0 ≤ V _I ≤ V _{DD}	0	0	5		470	1050		1200		1200	Ω	
					10		180	400		520		520		
					15		125	280		360		360		
Δ _{ON}	Resistance Δ _{RON} (between any 2 of 4 switches)	0 ≤ V _I ≤ V _{DD}	0	0	5		10						Ω	
					10		10							
					15		5							
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100		1000		1000	nA	
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18		±0.1	100		1000		1000	nA	
C _I	Input Capacitance		-5	-5	5		5						pF	
C _O	Output Capacitance						30							
C _{IO}	Feedthrough						0.2							
CONTROL (Address or Inhibit)														
V _{IL}	Input Low Voltage	= VDD thru 1KΩ	V _{EE} = V _{SS} R _L = 1KΩ to V _{SS} I _{IS} < 2μA (on all OFF channels)	5			1.5		1.5		1.5	V		
				10			3		3		3			
				15			4		4		4			
V _{IH}	Input High Voltage			5	3.5			3.5		3.5			V	
				10	7			7		7				
				15	11			11		11				
I _{IH} , I _{IL}	Input Leakage Current	V _I = 0/18V			18		±10 ⁻³	±0.1		±1		±1	μA	
C _I	Input Capacitance						5	7.5					pF	

* Determined by minimum feasible leakage measurement for automating testing.

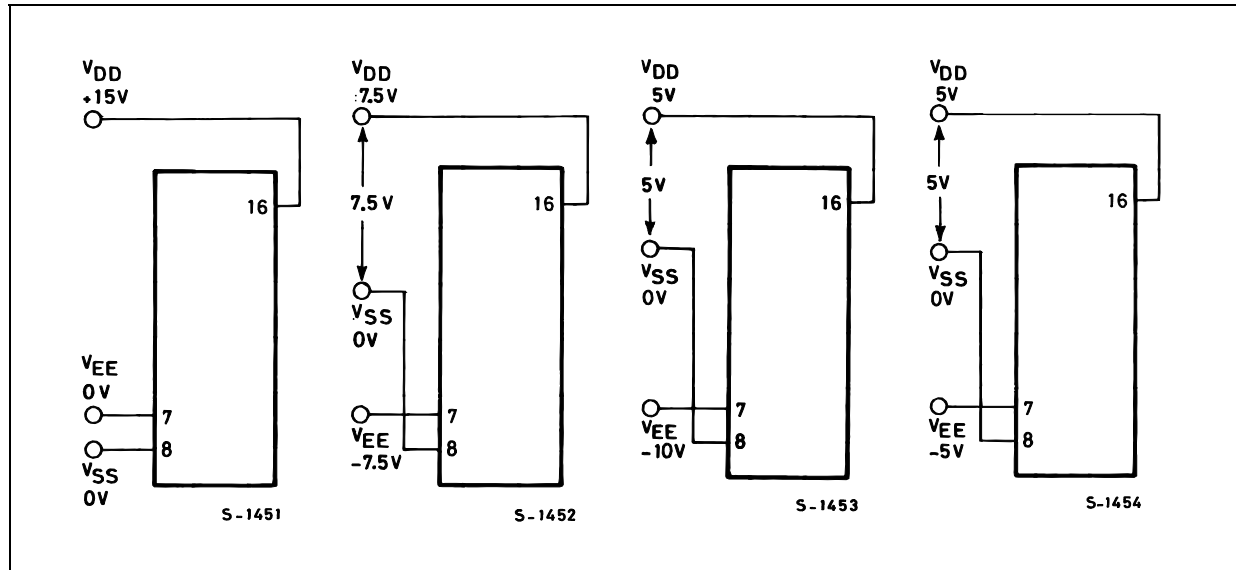
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, all input square wave rise and fall time = 20 ns)

Parameter	Test Condition							Value			Unit
	V _{EE} (V)	R _L (KΩ)	f _I (KHz)	V _I (V)	V _{SS} (V)	V _{DD} (V)		Min.	Typ.	Max.	
Propagation Delay Time (signal input to output)		200		V _{DD} 		5			30	60	ns
						10			15	30	
						15			11	20	
Frequency Response Channel "ON" (sine wave input) at 20 log V _O /V _I = - 3dB	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		20		MHz
							V _O at any channel		60		
Feedthrough (all channels OFF) at 20 log V _O /V _I = - 40dB	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		12		MHz
							V _O at any channel		8		
Frequency Signal Crosstalk at 20 log V _O /V _I = -40dB	= V _{SS}	1		5(*)		10	Between any 2 channels		3		MHz
Sine Wave Distortion f _{IS} = 1KHz Sine Wave	= V _{SS}	10	1	2(*)		5			0.3		%
				3(*)		10			0.2		
				5(*)		15			0.12		
CONTROL (Address or Inhibit)											
Propagation Delay: Address to Signal OUT (Channels ON or OFF)	0				0	5			360	720	ns
	0				0	10			160	320	
	0				0	15			120	240	
	-5				0	5			225	450	
Propagation Delay: Inhibit to Signal OUT (Channel turning ON)	0	1			0	5			360	720	ns
	0				0	10			160	320	
	0				0	15			120	240	
	-10				0	5			200	400	
Propagation Delay: Inhibit to Signal OUT (Channel turning OFF)	0	10				5			200	450	ns
	0					10			90	210	
	0					15			70	160	
	-10					5			130	300	
Address or Inhibit to Signal Crosstalk	0	10 ⁽¹⁾			0	10	V _C = V _{DD} -V _{SS} (square wave)		65		mV peak

(1) Both ends of channel.

* Peak to Peak voltage symmetrical about $(V_{DD} - V_{EE}) / 2$

TYPICAL BIAS VOLTAGES



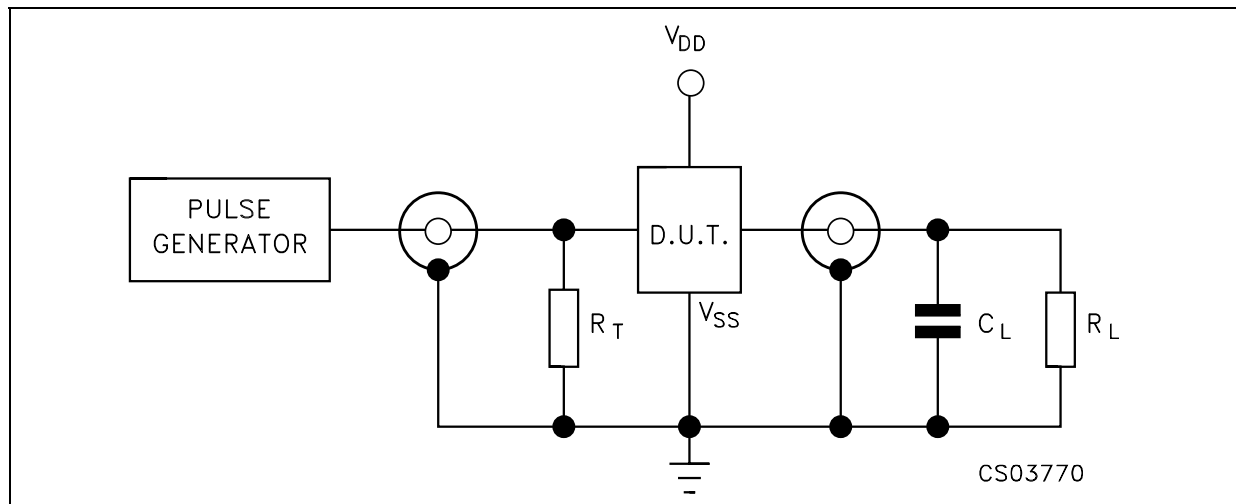
The ADDRESS (digital-control inputs) and INHIBIT logic levels are : "0"= V_{SS} and "1"= V_{DD} . The analog signal (through the TG) may swing from V_{EE} to V_{DD} .

SPECIAL CONSIDERATIONS

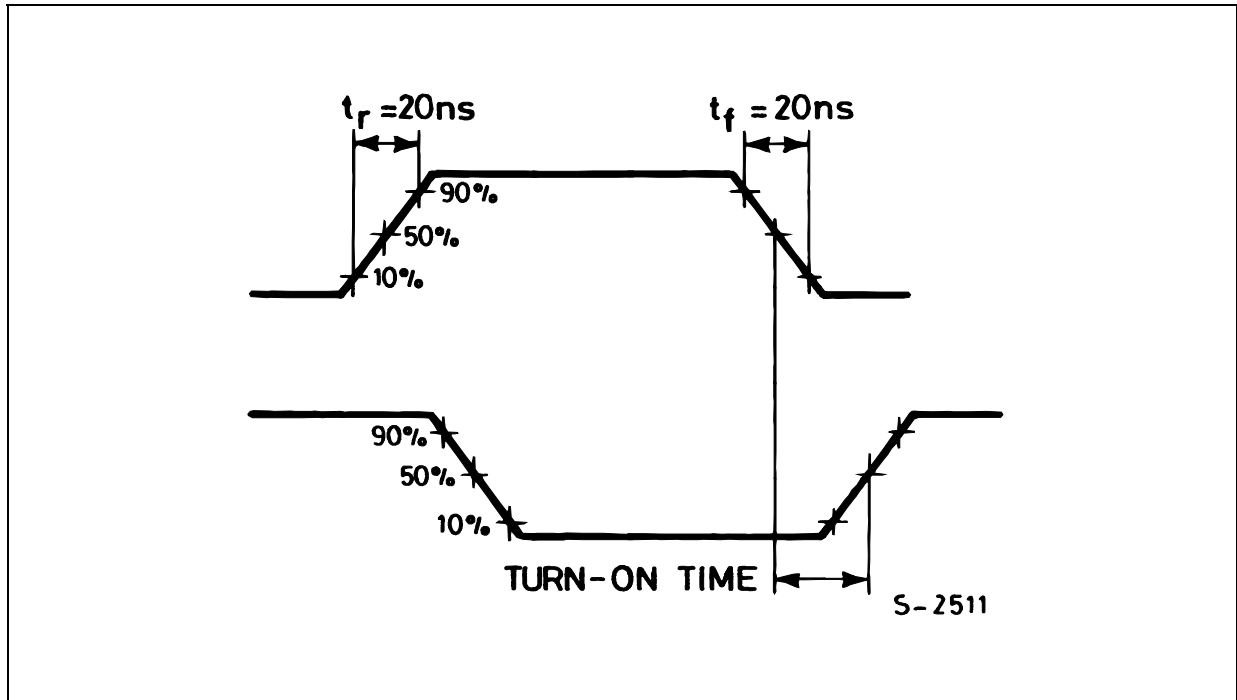
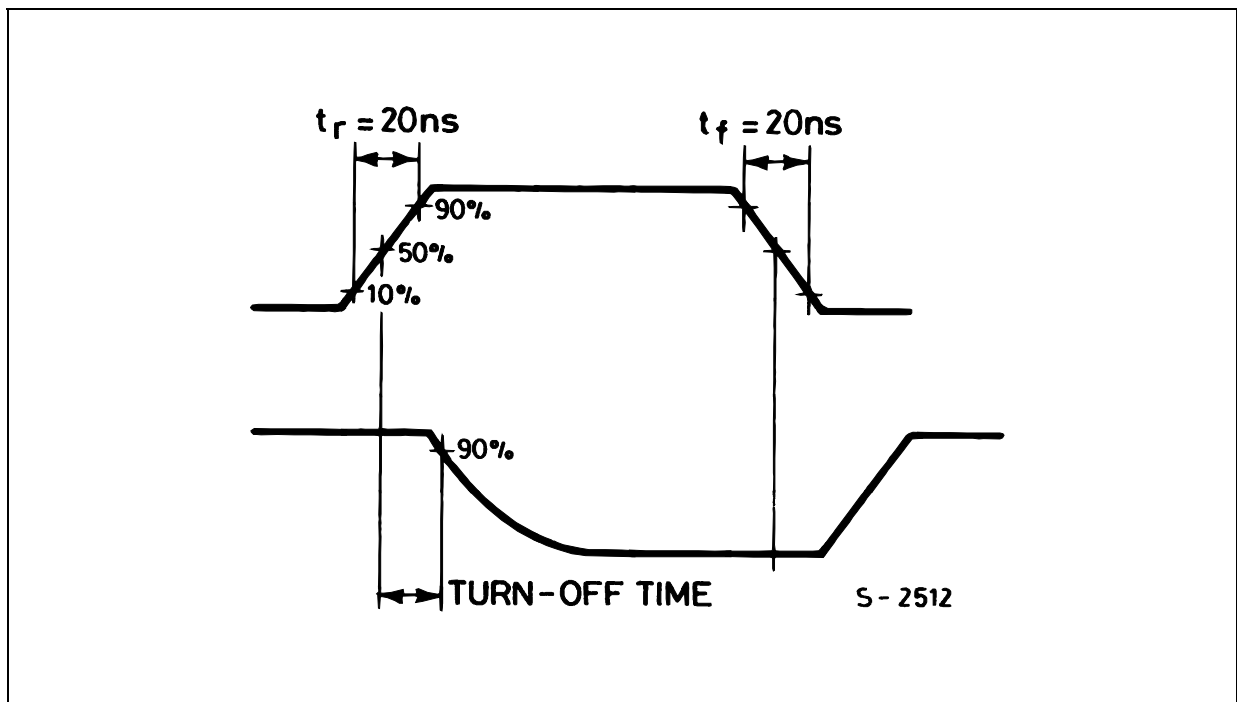
Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if $V_{DD} - V_{SS} = 3V$, a $V_{DD} - V_{EE}$ of up to 13V can be controlled; for $V_{DD} - V_{EE}$ level differences above 13V, a $V_{DD} - V_{SS}$ of at least 4.5V is required. For example, if $V_{DD} = +5$, $V_{SS} = 0$, and $V_{EE} = -13.5$, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In

certain applications, the external load resistor current may include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8V (calculated from R_{ON} values shown in DC SPECIFICATIONS). No V_{DD} current will flow through R_L if the switch current flows into lead 3.

TEST CIRCUIT

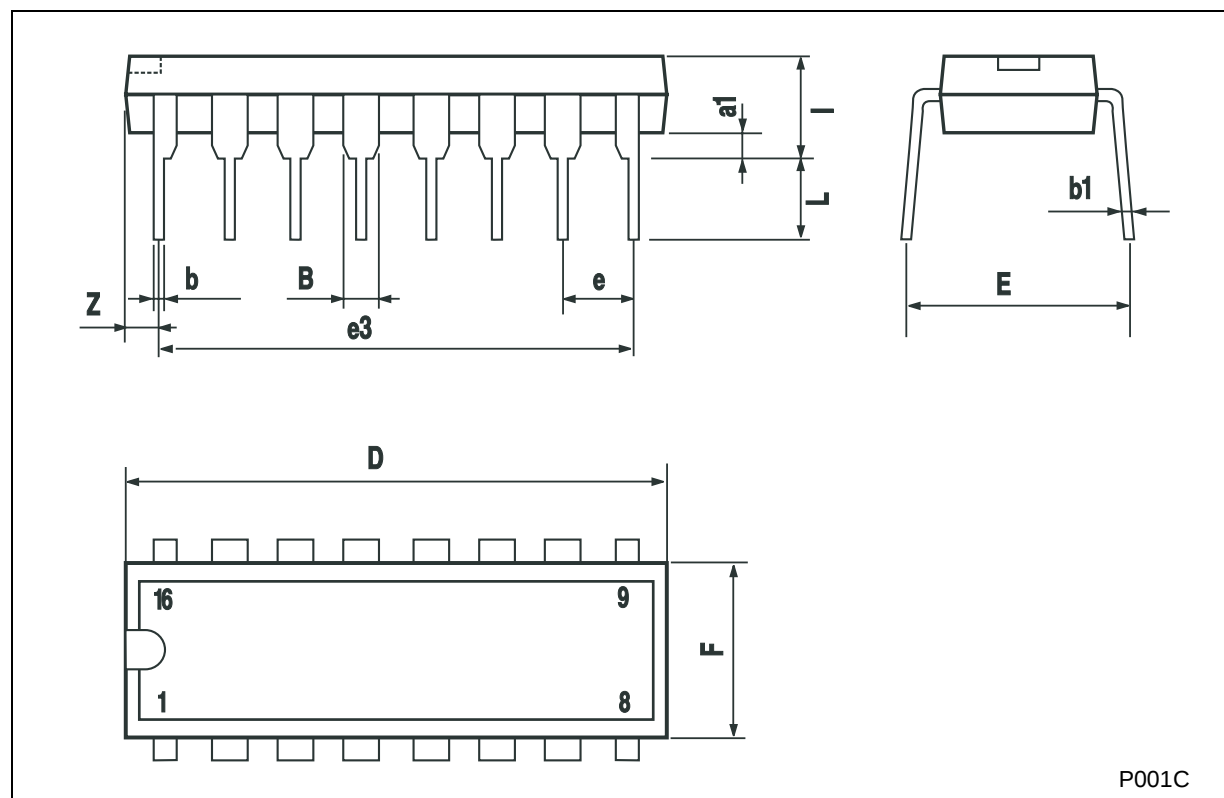


$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)
 $R_L = 200\text{K}\Omega$
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1 : CHANNEL BEING TURNED ON ($R_L = 1K\Omega$, $f=1MHz$; 50% duty cycle)**WAVEFORM 2 : CHANNEL BEING TURNED OFF** ($R_L = 1K\Omega$, $f=1MHz$; 50% duty cycle)

Plastic DIP-16 (0.25) MECHANICAL DATA

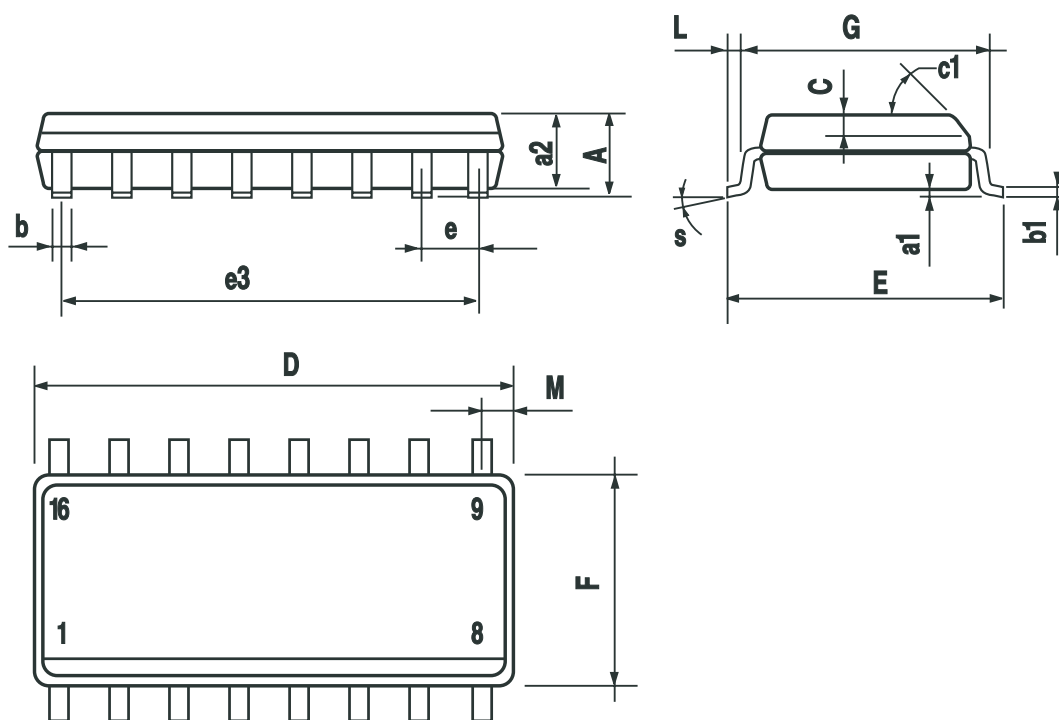
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



PO13H

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